

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC2937

DESCRIPTION

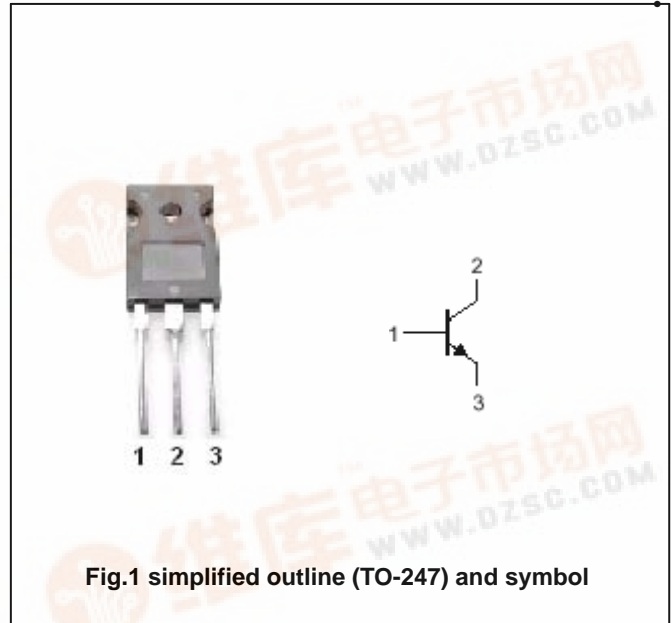
- With TO-247 package
- Switching power transistor
- High breakdown voltage

APPLICATIONS

- For switching regulator applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	500	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current (DC)		8	A
I _{CM}	Collector current-Peak		16	A
P _D	Total power dissipation	T _C =25°C	80	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A; I _B =0	400			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =4A; I _B =0.8A			1.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =4A; I _B =0.8A			1.5	V
I _{CBO}	Collector cut-off current	At rated voltage			0.1	mA
I _{CEO}	Collector cut-off current					
I _{EBO}	Emitter cut-off current	At rated voltage			0.1	mA
h _{FE-1}	DC current gain	I _C =4A; V _{CE} =2V	10		50	
h _{FE-2}	DC current gain	I _C =1mA; V _{CE} =2V	5			
f _T	Transition frequency	I _C =0.8A; V _{CE} =10V		20		MHz

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PACKAGE OUTLINE

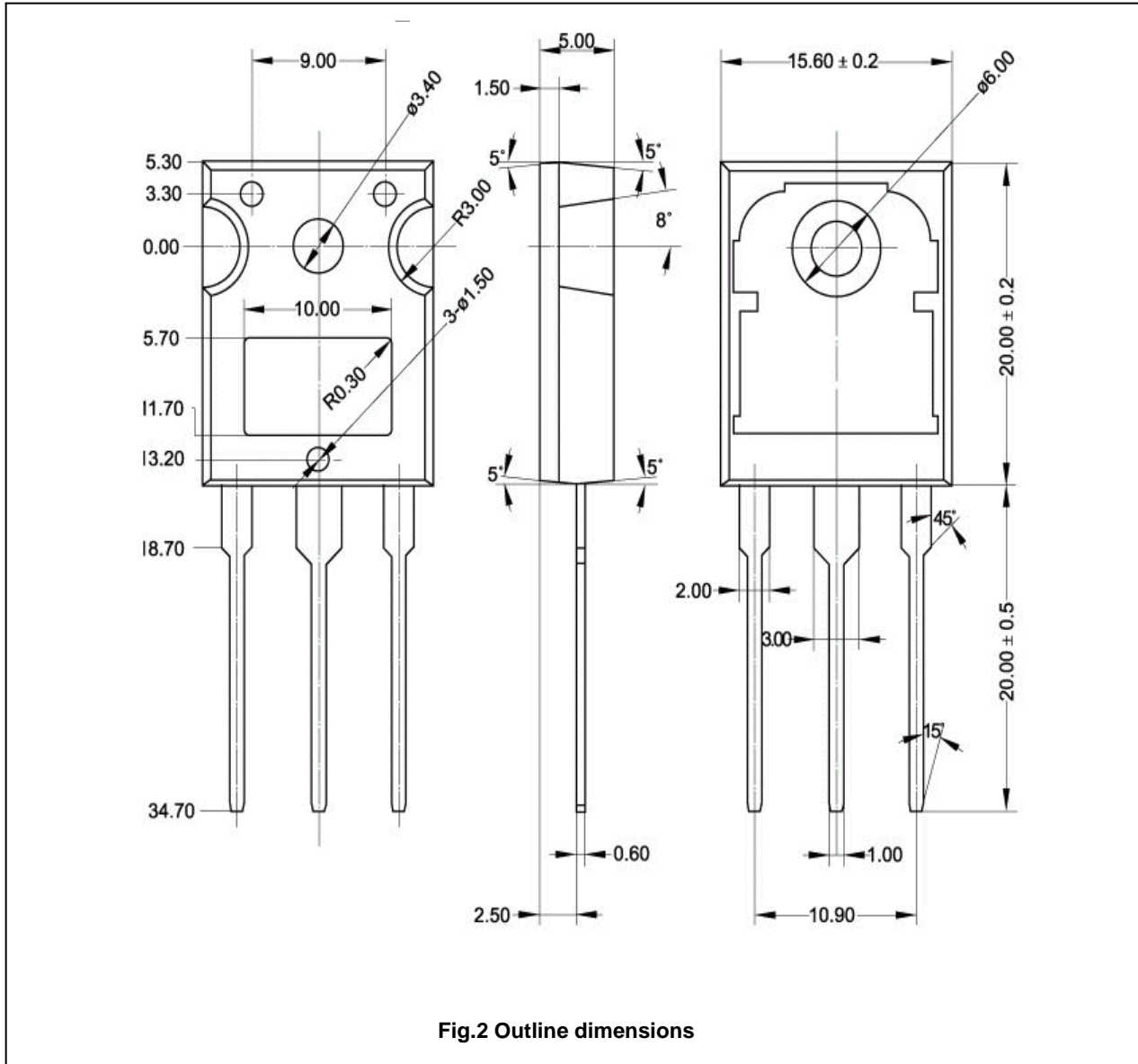


Fig.2 Outline dimensions